

wafer is raised at a rate of 50 to 200°C/s and then cooled at a rate of 20 to 100°C/s.

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(112)
1 (112) 33. A method according to claim 29 wherein said semiconductor film is crystallized by said heating while said semiconductor film is in contact with a silicon nitride film.--

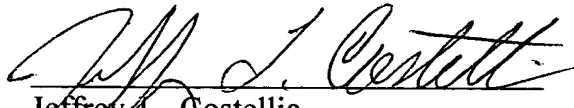
REMARKS

Claims 1-18 are cancelled herein and new claims 19-33 are added.

New claims 19-33 are directed to a different aspect of the present invention. The claimed annealed conditions, namely, the rates of heating and cooling, are disclosed in page 18 of the original application. Also, the non (111) plane feature as recited in claim 29 is supported by the original specification at line 25 of page 25, for example. These features are not disclosed or suggested in any of the cited references.

Examination on the merits is requested.

Respectfully submitted,


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